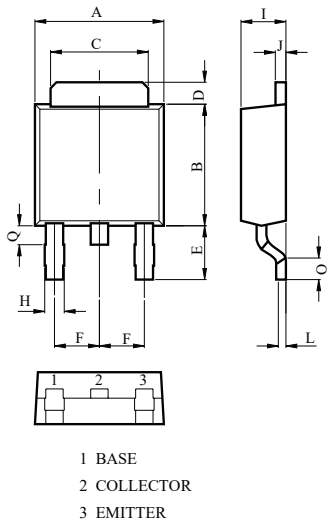
TRANSISTOR (PNP)



DIM	MILLIMETERS
A	6 50 ± 0 2
B	5 60 ± 0 2
C	5 20 ± 0 2
D	1 50 ± 0 2
E	2 70 ± 0 2
F	2 30 ± 0 1
H	1 00 MAX
I	2 30 ± 0 2
J	0 5 ± 0 1
L	0 50 ± 0 10
O	1 6 ± 0 2
Q	0 95 MAX

1 BASE
2 COLLECTOR
3 EMITTER

D-PAK (TO-252)

FEATURES

- Designed for General Purpose Amplifier and Low Speed Switching Applications
- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("–1" Suffix)
- Lead Formed Version in 16 mm Tape and Reel ("T4" Suffix)
- Electrically Similar to Popular TIP31 and TIP32 Series
- AEC-Q101 qualified

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1.25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65-150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= -1mA, I_E=0	-100		V
Collector-emitter breakdown voltage *	$V_{CEO(sus)}$	I_C= -30mA, I_B=0	-100		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -1mA, I_C=0	-5		V
Collector cut-off current	I_{CES}	V_{CE}=-100V, V_{EB}=0		-20	μA
Collector cut-off current	I_{CEO}	V_{CE}= -60V, I_B= 0		-50	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V, I_C=0		-1	mA
DC current gain	$h_{FE(1)}$	V_{CE}= -4V, I_C=-1A	25		
	$h_{FE(2)}$	V_{CE}=-4 V, I_C=-3A	15	75	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-3A, I_B=-0.375A		-1.2	V
Base-emitter voltage	$V_{BE(on)}$	V_{CE}= -4V, I_C=-3A		-1.8	V
Transition frequency	f_T	V_{CE}=-10V , I_C=-0.5A,f_T=1KHz	3		MHz

* Pulse Test: PW≤300μs, Duty Cycle≤2%.

Typical Characteristics